



PRELIMINARY DATA SHEET

UGF18060

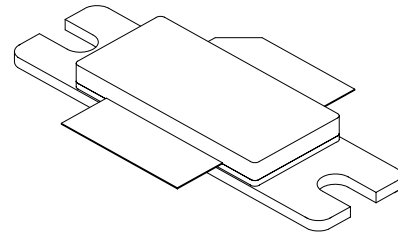
60W, 1.8 GHz, 26V Broadband RF Power N-Channel Enhancement-Mode Lateral MOSFET

Designed for DCS base station applications in the frequency band 1.805 to 1.88 GHz. Rated with a minimum output power of 60W. It is ideal for CDMA, TDMA, WCDMA, GSM, and Multi-Carrier Power Amplifiers in Class AB operation.

- ALL GOLD metal system for highest reliability
- Industry standard package
- Suggested alternative to the MRF18060
- Internally matched for repeatable manufacturing
- High gain, high efficiency and high linearity

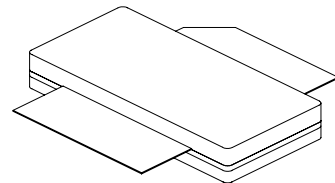
- **Application Specific Performance, 1.88 GHz**

GSM:	60 Watts	12.5 dB
EDGE:	25 Watts	12.5 dB
IS95 CDMA:	7.5 Watts	12.5 dB
CDMA2000:	TBD Watts	12.5 dB



Package Type 440171

PN: UGF18060F



Package Type 440172

PN: UGF18060P



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Maximum Ratings

Rating	Symbol	Value	Unit
Drain to Source Voltage, Gate connected to Source	V_{DSS}	65	Volts
Gate to Source Voltage	V_{GSS}	+15 to -0.5	Volts
Total Device Dissipation @ Tcase = 60°C Derate above 60°C	P_D	65 0.83	Watts W/°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Operating Junction Temperature	T_J	200	°C

Thermal Characteristics

Characteristic	Symbol	Typical	Unit
Thermal Resistance, Junction to Case	θ_{JC}	-	°C/W

Electrical DC Characteristics (T_C=25°C unless otherwise specified)

Rating	Symbol	Min	Typ	Max	Unit
Drain to Source Breakdown Voltage (V _{GS} =0, I _D =1mA)	BV_{DSS}	65	-	-	Volts
Drain to Source Leakage current (V _{DS} =26V, V _{GS} =0)	I_{DSS}	-	-	1.0	mA
Gate to Source Leakage current (V _{GS} =15V, V _{DS} =0)	I_{GSS}	-	-	1.0	μA
Threshold Voltage (V _{DS} =10V, I _D =1mA)	$V_{GS(th)}$	-	3.5	-	Volts
Gate Quiescent Voltage (V _{DS} =26 V, I _D =900mA)	$V_{GS(Q)}$	3.0	4.0	6.0	Volts
Drain to Source On Voltage (V _{GS} =10V, I _D =2A)	$V_{DS(on)}$	-	0.15	-	Volts
Forward Transconductance (V _{DS} =10V, I _D =5A)	G_m	-	-	-	S

AC Characteristics (T_C=25°C unless otherwise specified)

Rating	Symbol	Min	Typ	Max	Unit
Input Capacitance * (V _{DS} =26V, V _{GS} =0V, f = 1MHz)	C_{ISS}	-	-	-	pF
Output capacitance * (V _{DS} = 26V, V _{GS} =0V, f = 1MHz)	C_{OSS}	-	350	-	pF
Feedback capacitance * (V _{DS} =26V, V _{GS} =0V, f = 1MHz)	C_{RSS}	-	-	-	pF

* Part is internally matched on input and output.



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RF and Functional Tests (T_c=25°C unless otherwise specified, Cree Microwave Broadband Fixture)

Rating	Symbol	Min	Typ	Max	Unit
CW Small Signal Gain, P _{out} =10W V _{DD} =26V, I _{DQ} =500mA	G _L	-	12.5	-	dB
CW Power Gain, P _{out} = 60 W V _{DD} =26V, I _{DQ} =500mA	G _P	-	11.5	-	dB
CW Drain Efficiency, P _{out} = 60 W, f=1880 MHz, V _{DD} =26V, I _{DQ} =500mA,	η _D	-	36	-	%
Two-Tone Common-Source Amplifier Power Gain V _{DD} =26V, I _{DQ} =500mA, P _{out} = 60 W PEP f ₁ =1880 MHz and f ₂ =1880.1 MHz	G _{TT}	-	12	-	dB
Two-Tone Intermodulation Distortion V _{DD} =26V, I _{DQ} =500mA, P _{out} = 60 W PEP f ₁ =1880 MHz and f ₂ =1880.1 MHz	I _{MD}	-	-28	-	dBc
Two-Tone Drain Efficiency V _{DD} =26V, I _{DQ} =500mA, P _{out} = 60 W PEP f ₁ =1880 MHz and f ₂ =1880.1 MHz	η _{D2T}	-	38	-	%
Input Return Loss V _{DD} =26V, P _{out} = 60 W PEP, I _{DQ} =500mA f ₁ =1805 MHz and 1880 MHz, Tone Spacing = 100kHz	IRL	-	-10	-	dB
Load Mismatch Tolerance V _{DS} =26V, I _{DQ} = 500 mA, P _{out} =60W, f=1880 MHz	VSWR*	10:1	-	-	Ψ

Note (unless otherwise specified):

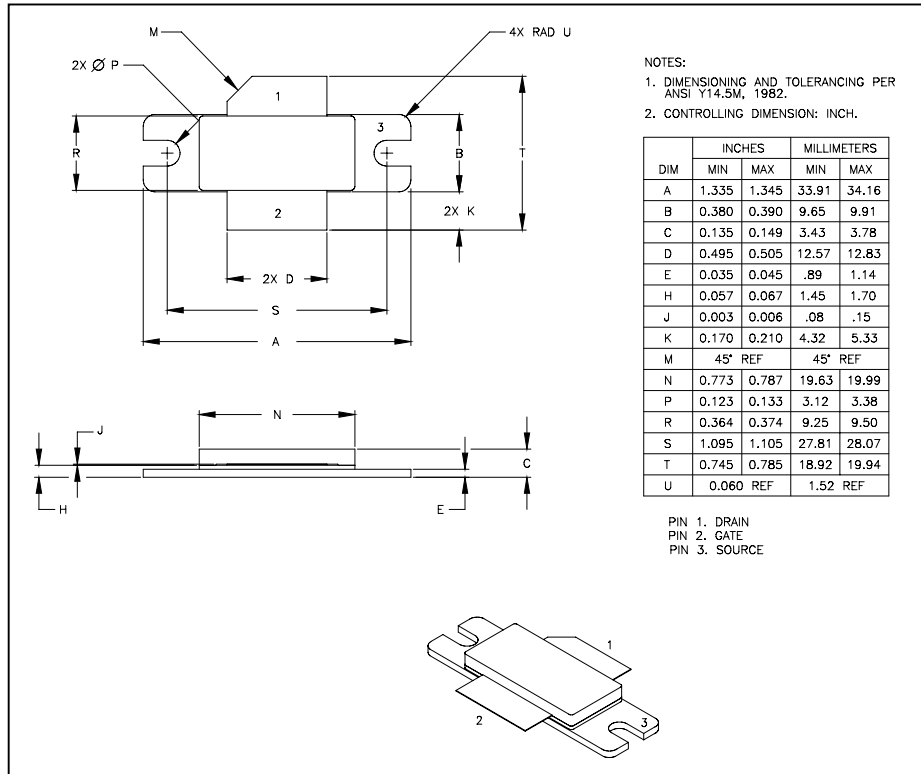
1. Source and load impedance shall be 50 ohms.

*No degradation in device performance after test.

CAUTION - MOS Devices are susceptible to damage from Electrostatic Discharge (ESD). Appropriate precautions in handling, packaging and testing MOS devices must be observed.

Product Dimensions

Package Number 440171



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